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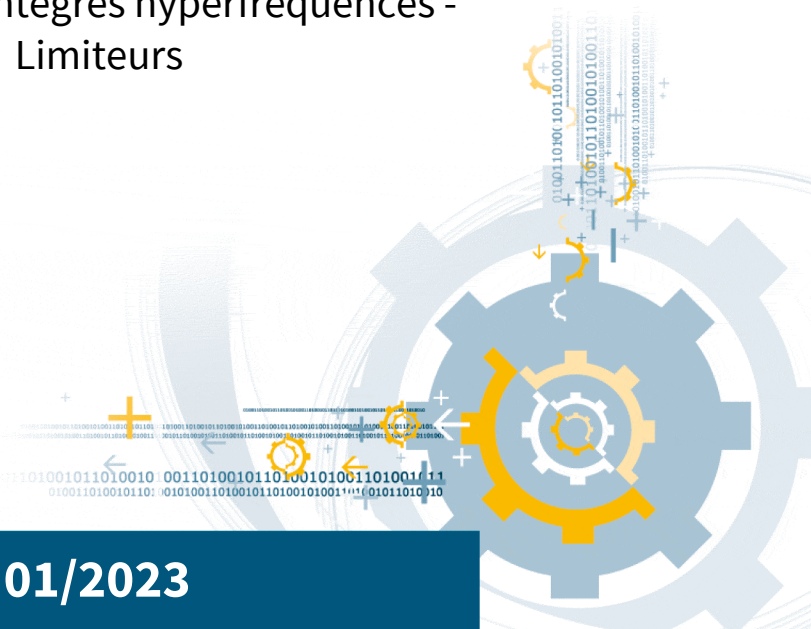
ILNAS-EN IEC 60747-16-8:2023

**Semiconductor devices - Part 16-8:
Microwave integrated circuits -
Limiters**

Halbleiterbauelemente - Teil 16-8:
Integrierte Mikrowellenschaltkreise -
Begrenzer

Dispositifs à semiconducteurs - Partie
16-8: Circuits intégrés hyperfréquences -
Limiteurs

01/2023



National Foreword

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ILNAS-EN IEC 60747-16-8:2023

EUROPEAN STANDARD **EN IEC 60747-16-8**

NORME EUROPÉENNE

EUROPÄISCHE NORM

January 2023

ICS 31.080.99

English Version

**Semiconductor devices - Part 16-8: Microwave integrated
circuits - Limiters
(IEC 60747-16-8:2022)**

Dispositifs à semiconducteurs - Partie 16-8: Circuits
intégrés hyperfréquences - Limiteurs
(IEC 60747-16-8:2022)

Halbleiterbauelemente - Teil 16-8: Integrierte Mikrowellen-
Verstärker - Schaltungsbegrenzer
(IEC 60747-16-8:2022)

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European Committee for Electrotechnical Standardization
Comité Européen de Normalisation Electrotechnique
Europäisches Komitee für Elektrotechnische Normung

CEN-CENELEC Management Centre: Rue de la Science 23, B-1040 Brussels

European foreword

The text of document 47E/793/FDIS, future edition 1 of IEC 60747-16-8, prepared by SC 47E "Discrete semiconductor devices" of IEC/TC 47 "Semiconductor devices" was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN IEC 60747-16-8:2023.

The following dates are fixed:

- latest date by which the document has to be implemented at national level by publication of an identical national standard or by endorsement (dop) 2023-10-03
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In the official version, for Bibliography, the following notes have to be added for the standard indicated:

IEC 60747-16-1:2001	NOTE Harmonized as EN 60747-16-1:2002 (not modified)
IEC 60747-16-1:2001/AMD1:2007	NOTE Harmonized as EN 60747-16-1:2002/A1:2007 (not modified)
IEC 60747-16-1:2001/AMD2:2017	NOTE Harmonized as EN 60747-16-1:2002/A2:2017 (not modified)
IEC 60747-16-4:2004	NOTE Harmonized as EN 60747-16-4:2004 (not modified)
IEC 60747-16-4:2004/AMD1:2009	NOTE Harmonized as EN 60747-16-4:2004/A1:2011 (not modified)
IEC 60747-16-4:2004/AMD2:2017	NOTE Harmonized as EN 60747-16-4:2004/A2:2017 (not modified)
IEC 60747-16-6:2019	NOTE Harmonized as EN IEC 60747-16-6:2019 (not modified)

Annex ZA (normative)

Normative references to international publications with their corresponding European publications

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

NOTE 1 Where an International Publication has been modified by common modifications, indicated by (mod), the relevant EN/HD applies.

NOTE 2 Up-to-date information on the latest versions of the European Standards listed in this annex is available here: www.cenelec.eu.

<u>Publication</u>	<u>Year</u>	<u>Title</u>	<u>EN/HD</u>	<u>Year</u>
IEC 60747-1	2006	Semiconductor devices - Part 1: General	-	-
+ A1	2010		-	-
IEC 60747-4	-	Semiconductor devices - Discrete devices -- Part 4: Microwave diodes and transistors		-
IEC 61340-5-1	-	Electrostatics - Part 5-1: Protection of electronic devices from electrostatic phenomena - General requirements	EN 61340-5-1	-
IEC/TR 61340-5-2	-	Electrostatics - Part 5-2: Protection of electronic devices from electrostatic phenomena - User guide	-	-



INTERNATIONAL STANDARD

NORME INTERNATIONALE

**Semiconductor devices –
Part 16-8: Microwave integrated circuits – Limiters**

**Dispositifs à semiconducteurs –
Partie 16-8: Circuits intégrés hyperfréquences – Limiteurs**

CONTENTS

FOREWORD	5
1 Scope	7
2 Normative references	7
3 Terms and definitions	7
4 Essential ratings and characteristics	9
4.1 General requirements	9
4.1.1 Circuit identification and types	9
4.1.2 General function description	9
4.1.3 Manufacturing technology	9
4.1.4 Package identification	9
4.1.5 Main application	9
4.2 Application description	10
4.2.1 Conformance to system and/or interface information	10
4.2.2 Overall block diagram	10
4.2.3 Reference data	10
4.2.4 Electrical compatibility	10
4.2.5 Associated devices	10
4.3 Specification of the function	10
4.3.1 Detailed block diagram – Functional blocks	10
4.3.2 Identification and function of terminals	11
4.3.3 Function description	11
4.4 Limiting values (absolute maximum rating system)	12
4.4.1 Requirements	12
4.4.2 Electrical limiting values	12
4.4.3 Temperatures	13
4.5 Operating conditions (within the specified operating temperature range)	13
4.6 Electrical characteristics	13
4.7 Mechanical and environmental ratings, characteristics and data	14
4.8 Additional information	14
5 Measuring methods	15
5.1 General	15
5.1.1 General precautions	15
5.1.2 Characteristic impedance	15
5.1.3 Handling precautions	15
5.1.4 Types	15
5.2 Insertion loss (L_{ins})	15
5.2.1 Purpose	15
5.2.2 Measuring methods	15
5.3 Input return loss ($L_{ret(in)}$)	18
5.3.1 Purpose	18
5.3.2 Measuring methods	19
5.4 Output return loss ($L_{ret(out)}$)	21
5.4.1 Purpose	21
5.4.2 Measuring methods	21
5.5 Input power at 1dB compression ($P_{i(1dB)}$) and output power at 1dB compression ($P_{o(1dB)}$)	24

5.5.1	Purpose	24
5.5.2	Circuit diagram	24
5.5.3	Principle of measurement	24
5.5.4	Circuit description and requirements	24
5.5.5	Precautions to be observed	24
5.5.6	Measurement procedure	24
5.5.7	Specified conditions	25
5.6	Intermodulation distortion (two-tone) (P_n/P_1)	25
5.6.1	Purpose	25
5.6.2	Circuit diagram	25
5.6.3	Principle of measurement	26
5.6.4	Circuit description and requirements	26
5.6.5	Precautions to be observed	26
5.6.6	Measurement procedure	27
5.6.7	Specified conditions	27
5.7	Power at the intercept point (for intermodulation products) ($P_{n(IP)}$)	27
5.7.1	Purpose	27
5.7.2	Circuit diagram	27
5.7.3	Principle of measurement	27
5.7.4	Circuit description and requirements	27
5.7.5	Precautions to be observed	27
5.7.6	Measurement procedure	28
5.7.7	Specified conditions	28
5.8	Leakage power for continuous wave ($P_{leak(cw)}$)	28
5.8.1	Purpose	28
5.8.2	Circuit diagram	28
5.8.3	Principle of measurement	29
5.8.4	Circuit description and requirements	29
5.8.5	Precautions to be observed	29
5.8.6	Measurement procedure	29
5.8.7	Specified conditions	30
5.9	Spike leakage power for pulse wave ($P_{leak(spike)}$) and flat leakage power for pulse wave ($P_{leak(flat)}$)	30
5.9.1	Purpose	30
5.9.2	Circuit diagram	30
5.9.3	Principle of measurement	30
5.9.4	Circuit description and requirements	30
5.9.5	Precautions to be observed	30
5.9.6	Measurement procedure	30
5.9.7	Specified conditions	31
5.10	Response time (t_{res})	31
5.10.1	Purpose	31
5.10.2	Circuit diagram	31
5.10.3	Principle of measurement	31
5.10.4	Circuit description and requirements	32
5.10.5	Precautions to be observed	32
5.10.6	Measurement procedure	32
5.10.7	Specified conditions	33

5.11	Recovery time(t_{rec}).....	33
5.11.1	Purpose	33
5.11.2	Circuit diagram	33
5.11.3	Principle of measurement	33
5.11.4	Circuit description and requirements.....	34
5.11.5	Precautions to be observed	34
5.11.6	Measurement procedure	34
5.11.7	Specified conditions.....	35
	Bibliography.....	36
	Figure 1 – Circuit diagram for the measurement of the insertion loss (method 1)	16
	Figure 2 – Circuit diagram for the measurement of the scattering parameters	17
	Figure 3 – Circuit diagram for the measurement of the input return loss (method 1).....	19
	Figure 4 – Circuit diagram for the measurement of the output return loss (method 1).....	22
	Figure 5 – Circuit diagram for the measurement of intermodulation distortion	25
	Figure 6 – Circuit diagram for the measurement of output leakage power	29
	Figure 7 – Circuit diagram for the measurement of response time.....	31
	Figure 8 – Spike leakage voltage and flat leakage voltage vs. time	32
	Figure 9 – Circuit diagram for the measurement of recovery time.....	33
	Figure 10 – Pulse envelope and continuous wave envelope vs. Time.....	34
	Table 1 – Function of terminals	11
	Table 2 – Electrical limiting values	12
	Table 3 – Electrical limiting values in detail specification	13
	Table 4 – Temperatures	13
	Table 5 – Electrical characteristics.....	14